

Order code	Manufacturer code	Description
82-1088	n/a	MC34063AP1G SWITCHING REGULATOR DIL-8 RC

	Page 1 of 14
The enclosed information is believed to be correct, Information may change ±without noticeqdue to	Revision A
product improvement. Users should ensure that the product is suitable for their use. E. & O. E.	20/02/2007

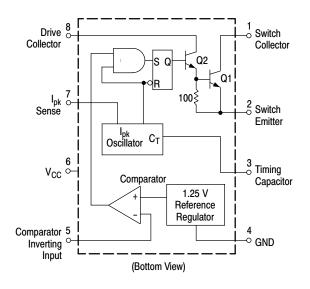
Technical: 01206 835555 Tech@rapidelec.co.uk Fax: 01206 751188 www.rapidonline.com

# **1.5 A, Step-Up/Down/** Inverting Switching Regulators

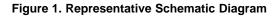
The MC34063A Series is a monolithic control circuit containing the primary functions required for DC-to-DC converters. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in Step-Down and Step-Up and Voltage-Inverting applications with a minimum number of external components. Refer to Application Notes AN920A/D and AN954/D for additional design information.

#### Features

- Operation from 3.0 V to 40 V Input
- Low Standby Current
- Current Limiting
- Output Switch Current to 1.5 A
- Output Voltage Adjustable
- Frequency Operation to 100 kHz
- Precision 2% Reference
- Pb–Free Packages are Available



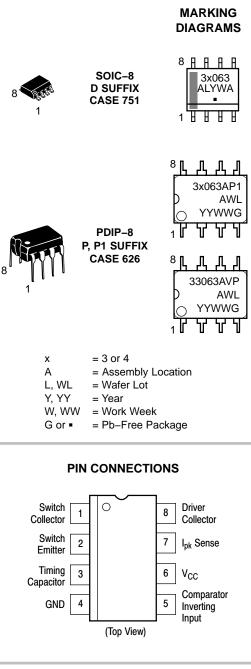
This device contains 51 active transistors.





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#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Power Supply Voltage	V <sub>CC</sub>	40	Vdc
Comparator Input Voltage Range	V <sub>IR</sub>	-0.3 to +40	Vdc
Switch Collector Voltage	V <sub>C(switch)</sub>	40	Vdc
Switch Emitter Voltage (V <sub>Pin 1</sub> = 40 V)	V <sub>E(switch)</sub>	40	Vdc
Switch Collector to Emitter Voltage	V <sub>CE(switch)</sub>	40	Vdc
Driver Collector Voltage	V <sub>C(driver)</sub>	40	Vdc
Driver Collector Current (Note 1)	I <sub>C(driver)</sub>	100	mA
Switch Current	I <sub>SW</sub>	1.5	А
Power Dissipation and Thermal Characteristics			
Plastic Package, P, P1 Suffix			
$T_A = 25^{\circ}C$	PD	1.25	W
Thermal Resistance	R <sub>θJA</sub>	100	°C/W
SOIC Package, D Suffix			
$T_A = 25^{\circ}C$	PD	625	mW
Thermal Resistance	$R_{ ext{ heta}JA}$	160	°C/W
Operating Junction Temperature	TJ	+150	°C
Operating Ambient Temperature Range	T <sub>A</sub>		°C
MC34063A		0 to +70	
MC33063AV, NCV33063A		-40 to +125	
MC33063A		-40 to +85	
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect Maximum package power dissipation limits must be observed.
 This device series contains ESD protection and exceeds the following tests: Human Body Model 4000 V per MIL-STD-883, Method 3015.

Machine Model Method 400 V.

3. NCV prefix is for automotive and other applications requiring site and change control.

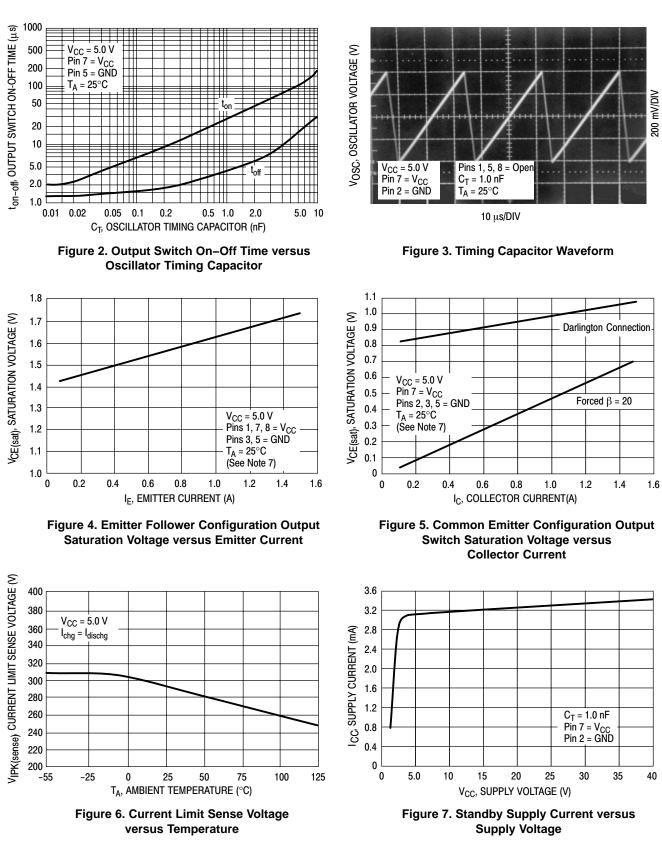
ELECTRICAL CHARACTERISTICS	$(V_{CC} = 5.0 \text{ V}, T_A = T_{low} \text{ to } T_{high} [N]$	lote 4], unless otherwise specified.)
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Characteristics	Symbol	Min	Тур	Max	Unit
OSCILLATOR					
Frequency (V <sub>Pin 5</sub> = 0 V, C <sub>T</sub> = 1.0 nF, T <sub>A</sub> = 25°C)	f <sub>osc</sub>	24	33	42	kHz
Charge Current (V <sub>CC</sub> = 5.0 V to 40 V, $T_A = 25^{\circ}C$ )	I <sub>chg</sub>	24	35	42	μA
Discharge Current (V <sub>CC</sub> = 5.0 V to 40 V, $T_A = 25^{\circ}C$ )	I <sub>dischg</sub>	140	220	260	μΑ
Discharge to Charge Current Ratio (Pin 7 to $V_{CC}$ , $T_A = 25^{\circ}C$ )	I <sub>dischg</sub> /I <sub>chg</sub>	5.2	6.5	7.5	-
Current Limit Sense Voltage ( $I_{chg} = I_{dischg}, T_A = 25^{\circ}C$ )	V <sub>ipk(sense)</sub>	250	300	350	mV
OUTPUT SWITCH (Note 5)					
Saturation Voltage, Darlington Connection (I <sub>SW</sub> = 1.0 A, Pins 1, 8 connected)	V <sub>CE(sat)</sub>	-	1.0	1.3	V
Saturation Voltage (Note 6) (I <sub>SW</sub> = 1.0 A, R <sub>Pin 8</sub> = 82 $\Omega$ to V <sub>CC</sub> , Forced $\beta \simeq$ 20)	V <sub>CE(sat)</sub>	-	0.45	0.7	V
DC Current Gain (I <sub>SW</sub> = 1.0 A, V <sub>CE</sub> = 5.0 V, T <sub>A</sub> = 25°C)	h <sub>FE</sub>	50	75	-	-
Collector Off-State Current (V <sub>CE</sub> = 40 V)	I <sub>C(off)</sub>	-	0.01	100	μΑ
COMPARATOR					
Threshold Voltage $T_A = 25^{\circ}C$ $T_A = T_{low}$ to $T_{high}$	V <sub>th</sub>	1.225 1.21	1.25 -	1.275 1.29	V
Threshold Voltage Line Regulation (V <sub>CC</sub> = 3.0 V to 40 V) MC33063A, MC34063A MC33063AV, NCV33063A	Reg <sub>line</sub>		1.4 1.4	5.0 6.0	mV
Input Bias Current (V <sub>in</sub> = 0 V)	I <sub>IB</sub>	-	-20	-400	nA
TOTAL DEVICE		-	•	-	
Supply Current (V <sub>CC</sub> = 5.0 V to 40 V, C <sub>T</sub> = 1.0 nF, Pin 7 = V <sub>CC</sub> , V <sub>Pin 5</sub> > V <sub>th</sub> , Pin 2 = GND, remaining pins open)	I <sub>CC</sub>	-	-	4.0	mA

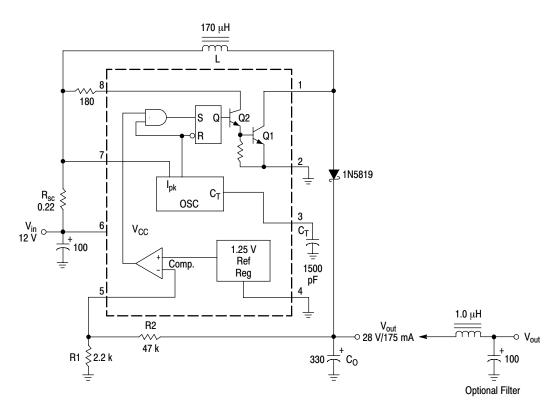
4. T<sub>low</sub> = 0°C for MC34063A, -40°C for MC33063A, AV, NCV33063A T<sub>high</sub> = +70°C for MC34063A, +85°C for MC33063A, +125°C for MC33063AV, NCV33063A
5. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible. 6. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 µs for it to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non-Darlington configuration is used, the following output drive condition is recommended:

Forced  $\beta$  of output switch :  $\frac{IC \text{ output}}{IC \text{ driver} - 7.0 \text{ mA}^*} \ge 10$ 

\* The 100  $\Omega$  resistor in the emitter of the driver device requires about 7.0 mA before the output switch conducts.



7. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.



Test	Conditions	Results	
Line Regulation	$V_{in}$ = 8.0 V to 16 V, I <sub>O</sub> = 175 mA	30 mV = ±0.05%	
Load Regulation	$V_{in}$ = 12 V, I <sub>O</sub> = 75 mA to 175 mA	10 mV = ±0.017%	
Output Ripple	$V_{in} = 12 \text{ V}, \text{ I}_{O} = 175 \text{ mA}$	400 mVpp	
Efficiency	V <sub>in</sub> = 12 V, I <sub>O</sub> = 175 mA	87.7%	
Output Ripple With Optional Filter	$V_{in} = 12 \text{ V}, \text{ I}_{O} = 175 \text{ mA}$	40 mVpp	

Figure 8. Step–Up Converter

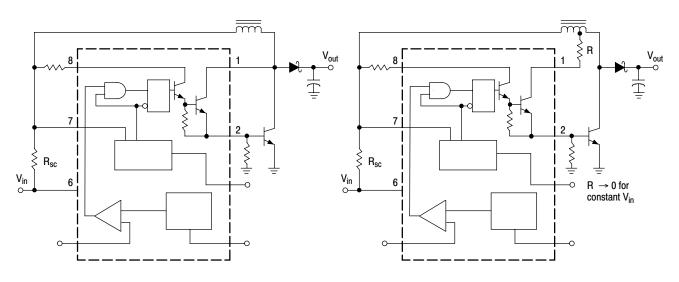
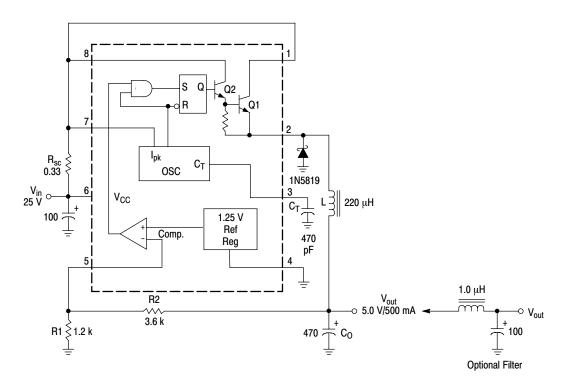


Figure 9. External Current Boost Connections for I<sub>C</sub> Peak Greater than 1.5 A

9a. External NPN Switch

9b. External NPN Saturated Switch (See Note 8)

8. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 µs to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non–Darlington configuration is used, the following output drive condition is recommended.



Test	Conditions	Results
Line Regulation	$V_{in}$ = 15 V to 25 V, I <sub>O</sub> = 500 mA	12 mV = ±0.12%
Load Regulation	$V_{in} = 25 \text{ V}, I_O = 50 \text{ mA to } 500 \text{ mA}$	3.0 mV = ±0.03%
Output Ripple	$V_{in} = 25 \text{ V}, \text{ I}_{O} = 500 \text{ mA}$	120 mVpp
Short Circuit Current	$V_{in}$ = 25 V, $R_L$ = 0.1 $\Omega$	1.1 A
Efficiency	$V_{in} = 25 \text{ V}, \text{ I}_{O} = 500 \text{ mA}$	83.7%
Output Ripple With Optional Filter	$V_{in} = 25 \text{ V}, \text{ I}_{O} = 500 \text{ mA}$	40 mVpp

Figure 10. Step-Down Converter

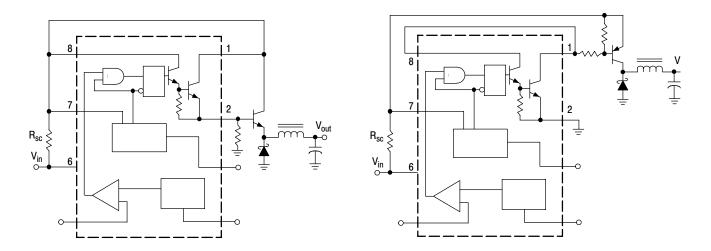
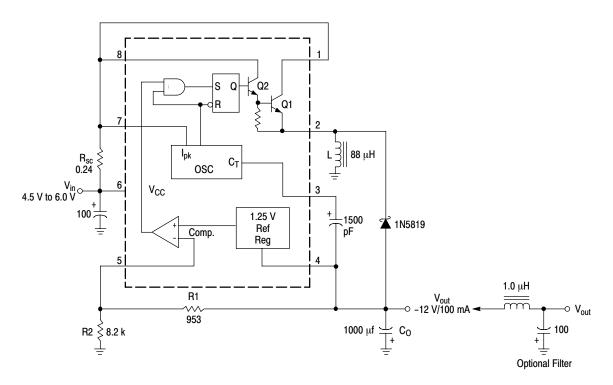


Figure 11. External Current Boost Connections for I<sub>C</sub> Peak Greater than 1.5 A

11a. External NPN Switch

11b. External PNP Saturated Switch



Test	Conditions	Results
Line Regulation	$V_{in}$ = 4.5 V to 6.0 V, I <sub>O</sub> = 100 mA	3.0 mV = ±0.012%
Load Regulation	$V_{in}$ = 5.0 V, I <sub>O</sub> = 10 mA to 100 mA	$0.022 \text{ V} = \pm 0.09\%$
Output Ripple	$V_{in} = 5.0 \text{ V}, I_{O} = 100 \text{ mA}$	500 mVpp
Short Circuit Current	$V_{in}$ = 5.0 V, R <sub>L</sub> = 0.1 $\Omega$	910 mA
Efficiency	$V_{in} = 5.0 \text{ V}, I_O = 100 \text{ mA}$	62.2%
Output Ripple With Optional Filter	$V_{in} = 5.0 \text{ V}, I_O = 100 \text{ mA}$	70 mVpp

Figure 12. Voltage Inverting Converter

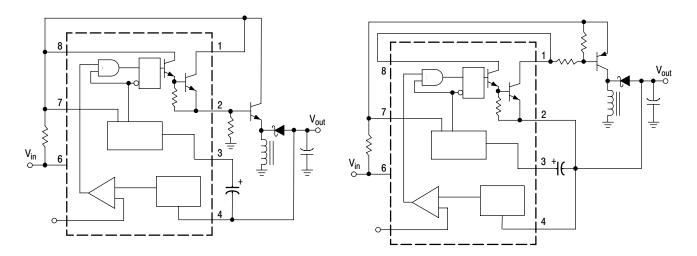
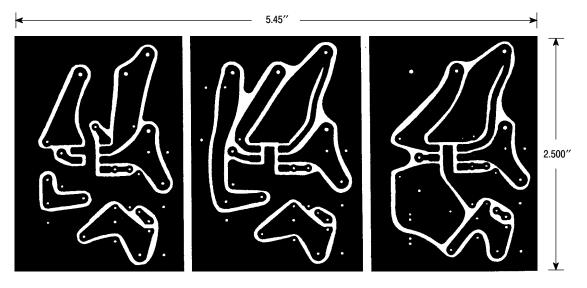
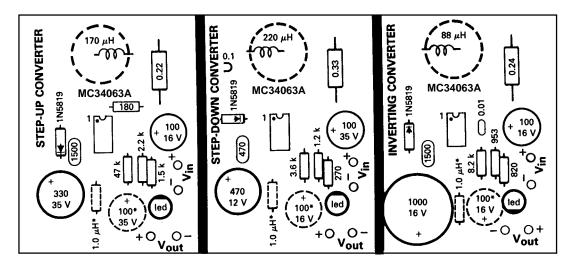


Figure 13. External Current Boost Connections for I<sub>C</sub> Peak Greater than 1.5 A13a. External NPN Switch13b. External PNP Saturated Switch



(Top view, copper foil as seen through the board from the component side)



(Top View, Component Side)

\*Optional Filter.

#### Figure 14. Printed Circuit Board and Component Layout (Circuits of Figures 8, 10, 12)

#### INDUCTOR DATA

Converter	Inductance (µH)	Turns/Wire			
Step-Up	170	38 Turns of #22 AWG			
Step-Down	220	48 Turns of #22 AWG			
Voltage-Inverting	88	28 Turns of #22 AWG			

All inductors are wound on Magnetics Inc. 55117 toroidal core.

Calculation	Step–Up	Step-Down	Voltage-Inverting
t <sub>on</sub> /t <sub>off</sub>	$\frac{V_{out}\ +\ V_{F}\ -\ V_{in(min)}}{V_{in(min)}\ -\ V_{sat}}$	Vout + V <sub>F</sub> V <sub>in(min)</sub> - V <sub>sat</sub> - V <sub>out</sub>	$\frac{ V_out  \ + \ V_F}{V_in \ - \ V_sat}$
$(t_{on} + t_{off})$	$\frac{1}{f}$	<u>1</u> f	<u>1</u> f
t <sub>off</sub>	$\frac{\frac{t_{on} + t_{off}}{\frac{t_{on}}{t_{off}} + 1}$	$\frac{\frac{t_{on} + t_{off}}{\frac{t_{on}}{t_{off}} + 1}$	$\frac{\frac{t_{on} + t_{off}}{t_{off}}}{\frac{t_{on}}{t_{off}} + 1}$
t <sub>on</sub>	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$	$(t_{on} + t_{off}) - t_{off}$
CT	4.0 x 10 <sup>-5</sup> t <sub>on</sub>	4.0 x 10 <sup>-5</sup> t <sub>on</sub>	4.0 x 10 <sup>-5</sup> t <sub>on</sub>
I <sub>pk(switch)</sub>	$2I_{out(max)}\left(\frac{t_{on}}{t_{off}} + 1\right)$	<sup>2I</sup> out(max)	$2I_{out(max)}\left(\frac{t_{on}}{t_{off}} + 1\right)$
R <sub>sc</sub>	0.3/I <sub>pk(switch)</sub>	0.3/I <sub>pk(switch)</sub>	0.3/I <sub>pk(switch)</sub>
L <sub>(min)</sub>	$\left( rac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}}  ight)^t$ on(max)	$\left(\frac{(V_{in(min)} - V_{sat} - V_{out})}{I_{pk(switch)}}\right)t_{on(max)}$	$\left(rac{(V_{in(min)} - V_{sat})}{I_{pk(switch)}} ight)^{t}$ on(max)
C <sub>O</sub>	9 <mark>l<sub>out</sub>t<sub>on</sub> V<sub>ripple(pp)</sub></mark>	$\frac{I_{pk(switch)}(t_{on} + t_{off})}{^{8V}ripple(pp)}$	9 <mark>l<sub>out</sub>ton</mark> V <sub>ripple(pp)</sub>

 $V_{sat}$  = Saturation voltage of the output switch. V<sub>F</sub> = Forward voltage drop of the output rectifier.

### The following power supply characteristics must be chosen:

Vin - Nominal input voltage.

 $\begin{array}{l} V_{in} - \text{Nominal input voltage.} \\ V_{out} - \text{Desired output voltage, } |V_{out}| &= 1.25 \left(1 + \frac{R2}{R1}\right) \\ I_{out} - \text{Desired output current.} \\ f_{min} - \text{Minimum desired output switching frequency at the selected values of } V_{in} \text{ and } I_{O}. \end{array}$ 

Vripple(pp) - Desired peak-to-peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.

NOTE: For further information refer to Application Note AN920A/D and AN954/D.

#### Figure 15. Design Formula Table

#### **ORDERING INFORMATION**

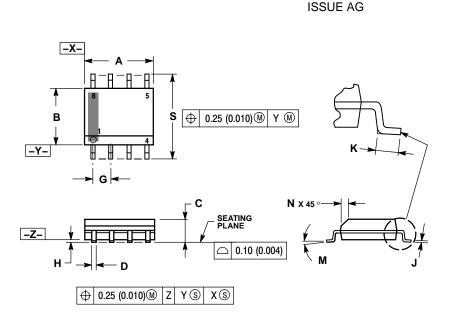
Device	Package	Shipping <sup>†</sup>	
MC33063AD	SOIC-8	98 Units / Rail	
MC33063ADG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC33063ADR2	SOIC-8	2500 Units / Tape & Reel	
MC33063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
MC33063AP1	PDIP-8	50 Units / Rail	
MC33063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail	
MC33063AVD	SOIC-8	98 Units / Rail	
MC33063AVDG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC33063AVDR2	SOIC-8		
MC33063AVDR2G	SOIC-8 (Pb-Free)		
NCV33063AVDR2*	SOIC-8	2500 Units / Tape & Reel	
NCV33063AVDR2G*	SOIC-8 (Pb-Free)		
MC33063AVP	PDIP-8	50 Units / Rail	
MC33063AVPG	PDIP-8 (Pb-Free)	50 Units / Rail	
MC34063AD	SOIC-8	98 Units / Rail	
MC34063ADG	SOIC-8 (Pb-Free)	98 Units / Rail	
MC34063ADR2	SOIC-8	2500 Units / Tape & Reel	
MC34063ADR2G	SOIC-8 (Pb-Free)	2500 Units / Tape & Reel	
MC34063AP1	PDIP-8	50 Units / Rail	
MC34063AP1G	PDIP-8 (Pb-Free)	50 Units / Rail	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

\*NCV33063A: T<sub>low</sub> = -40°C, T<sub>high</sub> = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

#### PACKAGE DIMENSIONS

SOIC-8 NB **D SUFFIX** CASE 751-07



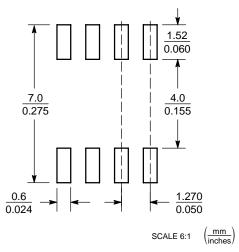
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) DEB SUB

- PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR DIMENSION DOES NOT INCLODE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION. 751-01 THRU 751-06 ARE OBSOLETE. NEW CTANDADUS 274.
- 6. STANDARD IS 751-07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
в	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
к	0.40	1.27	0.016	0.050
м	0 °	8 °	0 °	8 °
Ν	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

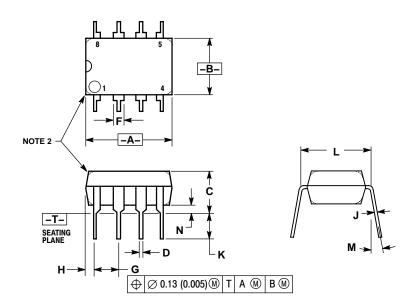
**SOLDERING FOOTPRINT\*** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS





NOTES:

1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL. 2. PACKAGE CONTOUR OPTIONAL (ROUND OR

SQUARE CORNERS). 3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.40	10.16	0.370	0.400
В	6.10	6.60	0.240	0.260
С	3.94	4.45	0.155	0.175
D	0.38	0.51	0.015	0.020
F	1.02	1.78	0.040	0.070
G	2.54 BSC		0.100 BSC	
Н	0.76	1.27	0.030	0.050
J	0.20	0.30	0.008	0.012
K	2.92	3.43	0.115	0.135
L	7.62 BSC		0.300 BSC	
М		10°		10°
Ν	0.76	1.01	0.030	0.040

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